	Document ID	Issue Date	Pages	Title	Current OR
1	US 6468853 B1	20021022	10	Method of fabricating a shallow trench isolation structure with reduced local oxide recess near corner	438/221
2	US 6376362 B1	20020423	7	Production of semiconductor device	438/633
3	US 6361646 B1	20020326	23	Method and apparatus for endpoint detection for chemical mechanical polishing	
4	US 6247998 B1	20010619	21	Method and apparatus for determining substrate layer thickness during chemical mechanical polishing	451/6
5	US 6166879 A	20001226	12	Thin film magnetic head with contoured surface	360/122
6	US 6095904 A	20000801	14	Orbital motion chemical-mechanical polishing method and apparatus	451/41
7	US 5940956 A	19990824	12	Chemical-mechanical contouring (CMC) method for forming a contoured surface	29/603.16
8	US 5930646 A	19990727	7	Method of shallow trench isolation	438/431
9	US 5876271 A	19990302	26	Slurry injection and recovery method and apparatus for chemical-mechanical polishing process	451/60
10	US 5720845 A	19980224	15	Wafer polisher head used for chemical-mechanical polishing and endpoint detection	156/345.13
11	US 5609511 A	19970311	18	Polishing method	451/5

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	1	438/424
	2	438/612; 438/642
	3	216/85; 216/88; 216/89; 216/90; 216/91; 438/14; 438/16; 438/690; 438/691; 438/692; 438/7; 438/8; 451/6
. *	4	451/41
	5	360/121
	6	451/173; 451/60
	7	29/603.01; 29/603.14; 29/603.15; 29/603.19; 29/603.25
	8	257/50; 438/224; 438/427
	9	451/41; 451/446
	10	216/86; 216/88; 438/14; 438/692
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12	US 5554064 A	19960910	18	Orbital motion chemical-mechanical polishing apparatus and method of fabrication	451/41
13	US 5547417 A	19960820		Method and apparatus for conditioning a semiconductor polishing pad	451/58
14	US 5216843 A	19930608	10	Polishing pad conditioning apparatus for wafer planarization process	451/285

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12	451/446; 451/505; 451/60
13	451/443
14	451/287; 451/36; 451/398; 451/446; 451/550; 451/56